

FORM PTO- 1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 0139376	SERIAL NO 10/799,554
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT Rommel, et al.	
		FILING DATE March 10, 2004	GROUP 2814

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
HP	6,500,724	12/31/02	Zurcher et al.			
	6,180,976	1/30/01	Roy			
	5,926,359	7/20/99	Greco et al.			
	5,731,747	3/24/98	Van De Walle, et al.			
	5,708,559	1/13/98	Brabazon, et al.			
HP	6,117,747	9/12/00	Shao, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
HP	2000228497	8/15/00	Japan			No	

OTHER DOCUMENTS (Including Author, Title, Date Pertinent Pages, Etc.)

HP		Yoshitomi et al., <u>High Performance MIM Capacitor for RF BiCMOS/CMOS LSIs</u> ; <i>Proc. of the BCTM</i> , pp. 133-36, 1999.
HP		Lui et al., <u>Single Mask Metal-Insulator-Metal (MIM) Capacitor with Copper Damascene Metallization for Sub-0.18μm Mixed Mode Signal and System-on-a-Chip (SoC) Applications</u> ; <i>IEEE</i> , pp. 111-13, 2000.
HP		Mahnkopf et al., <u>'System on a Chip' Technology Platform for 0.18μm Digital, Mixed Signal & eDRAM Applications</u> , <i>IEDM</i> , pp. 849-52, 1999.
HP		Bolam et al., <u>Electrical Characteristics and Reliability of UV Transparent Si₃N₄ Metal-Insulator-Metal (MIM) Capacitors</u> , <i>IEEE Transactions on Electron Devices</i> , Vol. 50, No. 4, pp. 941-44, 2003.

EXAMINER

Waylam

2/28/05

DATE
CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in the conformance and not considered. Include copy of this form with next communication to applicant.

(Form PTO-1449)